Transistors Panasonic

2SA2163

Silicon PNP epitaxial planar type

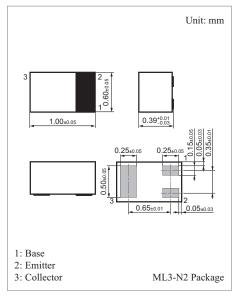
For high frequency amplification

■ Features

- ullet High transition frequency f_T
- Optimum for high-density mounting and downsizing of the equipment for Ultraminiature leadless package
 0.6 mm × 1.0 mm (height 0.39 mm)

■ Absolute Maximum Ratings $T_{a'} = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-30	V	
Collector-emitter voltage (Base open)	V _{CEO}	-20	V	
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	-5	V	
Collector current	I_{C}	-30	mA	
Collector power dissipation	P _C	100	mW	
Junction temperature	T_j	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	



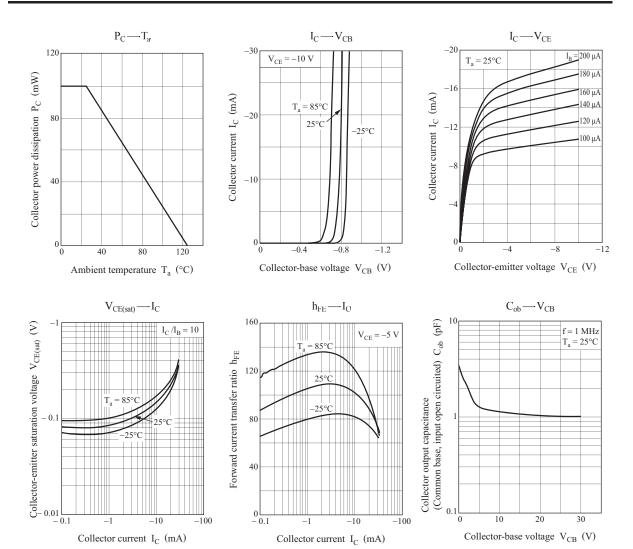
Marking Symbol: 6J

■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Base-emitter voltage	V_{BE}	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$		-0.7		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_{E} = 0$			-0.1	μА
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -20 \text{ V}, I_{B} = 0$			-100	μА
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-10	μА
Forward current transfer ratio	$h_{\rm FE}$	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}$	70		220	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$		-0.1		V
Transition frequency	\mathbf{f}_{T}	$V_{CB} = -10 \text{ V}, I_{H} = 1 \text{ mA}, f = 200 \text{ MHz}$	150	300		MHz
Noise figure	NF	$V_{CB} = -10 \text{ V}, I_{E} = 1 \text{ mA}, f = 5 \text{ MHz}$		2.8	4.0	dB
Reverse transfer impedance	Z _{rb}	$V_{CB} = -10 \text{ V}, I_H = 1 \text{ mA}, f = 2 \text{ MHz}$		22	50	Ω
Reverse transfer capacitance (Common emitter)	C _{re}	$V_{CB} = -10 \text{ V}, I_{E} = 1 \text{ mA}, f = 10.7 \text{ MHz}$		1.2	2.0	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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